

DMP2035U

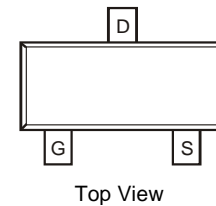
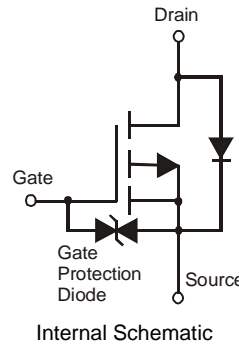
P-CHANNEL ENHANCEMENT MODE MOSFET

Features

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **ESD Protected Up To 3KV**
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Weight: 0.008 grams (approximate)

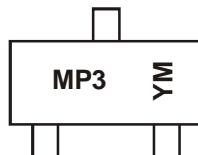


Ordering Information (Note 4)

Part Number	Qualification	Case	Packaging
DMP2035U-7	Commercial	SOT23	3000 / 7" Tape & Reel
DMP2035UQ-7	Automotive	SOT23	3000 / 7" Tape & Reel

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

Marking Information



MP3 = Product Type Marking Code
 YM = Date Code Marking
 Y = Year (ex: W = 2009)
 M = Month (ex: 9 = September)

Date Code Key

Year	2009	2010	2011	2012	2013	2014	2015
Code	W	X	Y	Z	A	B	C

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D



DMP2035U

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	-20	V
Gate-Source Voltage			V _{GSS}	±8	V
Continuous Drain Current (Note 5)	Steady State	T _A = +25°C	I _D	-3.6	A
		T _A = +70°C		-2.9	
Pulsed Drain Current (Note 6)			I _{DM}	-24	A

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P _D	0.81	W
Thermal Resistance, Junction to Ambient @T _A = +25°C	R _{θJA}	153.5	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	-20	-	-	V	V _{GS} = 0V, I _D = -250μA
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	-	-	-1.0	μA	V _{DS} = -20V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	-	-	±10	μA	V _{GS} = ±8V, V _{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(th)}	-0.4	-0.7	-1.0	V	V _{DS} = V _{GS} , I _D = -250μA
Static Drain-Source On-Resistance	R _{DS(on)}	-	23	35	mΩ	V _{GS} = -4.5V, I _D = -4.0A
			30	45		V _{GS} = -2.5V, I _D = -4.0A
			41	62		V _{GS} = -1.8V, I _D = -2.0A
Forward Transfer Admittance	Y _{fs}	-	14	-	S	V _{DS} = -5V, I _D = -4A
Diode Forward Voltage	V _{SD}	-	-0.7	-1.0	V	V _{GS} = 0V, I _S = -1A
DYNAMIC CHARACTERISTICS						
Input Capacitance	C _{iss}	-	1610	-	pF	V _{DS} = -10V, V _{GS} = 0V f = 1.0MHz
Output Capacitance	C _{oss}	-	157	-	pF	
Reverse Transfer Capacitance	C _{rss}	-	145	-	pF	
Gate Resistance	R _g	-	9.45	-	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge	Q _g	-	15.4	-	nC	V _{GS} = -4.5V, V _{DS} = -10V, I _D = -4A
Gate-Source Charge	Q _{gs}	-	2.5	-	nC	
Gate-Drain Charge	Q _{gd}	-	3.3	-	nC	
Turn-On Delay Time	t _{D(on)}	-	16.8	-	ns	V _{DS} = -10V, V _{GS} = -4.5V, R _L = 10Ω, R _G = 6.0Ω, I _D = -1A
Turn-On Rise Time	t _r	-	12.4	-	ns	
Turn-Off Delay Time	t _{D(off)}	-	94.1	-	ns	
Turn-Off Fall Time	t _f	-	42.4	-	ns	

- Notes:
3. Device mounted on FR-4 PCB with 2 oz. Copper and test pulse width t ≤ 10s.
 4. Repetitive rating, pulse width limited by junction temperature.
 5. Short duration pulse test used to minimize self-heating effect.